2SC3940, 2SC3940A

Silicon NPN epitaxial planar type

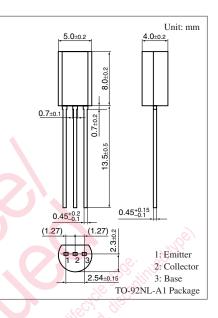
For low-frequency output amplification and driver amplification Complementary to 2SA1534, 2SA1534A

Features

- \bullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- Allowing supply with the radial taping

■ Absolute Maximum Ratings T_a = 25°C Parameter Symbol Rating

Falametei			Unit
2SC3940	V _{CBO}	30	v
2SC3940A		60	
2SC3940	V _{CEO}	25	v
2SC3940A		50	
Emitter-base voltage (Collector open)		5	V
Collector current			А
Peak collector current			A
Collector power dissipation		1	W
Junction temperature			°C
Storage temperature			°C
	2SC3940A 2SC3940 2SC3940A lector open)	$\begin{array}{c} \hline \hline \\ 2SC3940A \\ \hline \\ 2SC3940A \\ \hline \\ 2SC3940A \\ \hline \\ \hline \\ Lector open) \\ \hline \\ \hline \\ I_C \\ \hline \\ I_{CP} \\ \hline \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	U	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage	2SC3940	V _{CBO}	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	30			V
(Emitter open)	2SC3940A		TR. SHIT	60			
Collector-emitter voltage	2SC3940	V _{CEO}	$I_{\rm C} = 2 \ {\rm mA}, \ I_{\rm B} = 0$	25			V
(Base open)	2SC3940A		O'ES (I'S.	50			
Emitter-base voltage (Colle	ctor open)	V _{EBO}	$I_E = 10 \ \mu A, \ I_C = 0$	5			V
Collector-base cutoff current (Emitter open)		I _{CBO}	$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0$			0.1	μΑ
Forward current transfer rat	io *1 🔬	h _{FE1} *2	$V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA}$	85		340	—
		h _{FE2}	$V_{CE} = 5 V, I_C = 1 A$	50			_
Collector-emitter saturation	voltage*1	V _{CE(sat)}	$I_{C} = 500 \text{ mA}, I_{B} = 50 \text{ mA}$		0.2	0.4	V
Base-emitter saturation volt	tage ^{*1}	V _{BE(sat)}	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$		0.85	1.20	V
Transition frequency	0	f _T	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance		C _{ob}	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$		11	20	pF
(Common base, input open circuited)							

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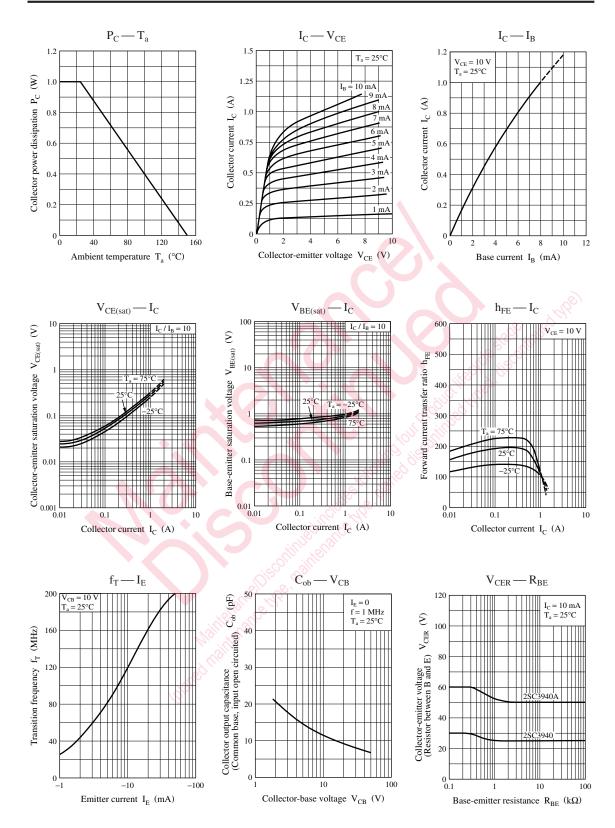
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

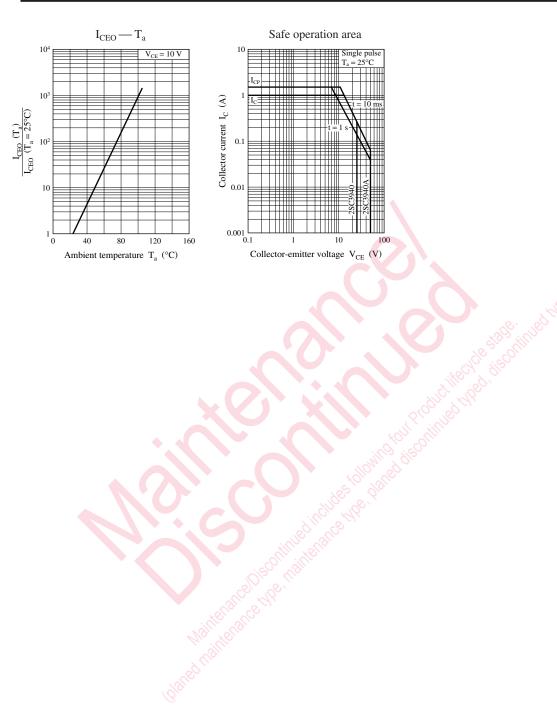
*2: Rank classification

Rank	Q	R	S
h_{FE1}	85 to 170	120 to 240	170 to 340

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